Docket No. A545MMP (121116.00009)

In the Specification:

Please Amend the Specification as follows:

Please replace the first full paragraph on page 8 of the Specification (lines 8 through 21) with the following:

device 80, according to the invention. The device 80 comprises a transistor 82, or

other similar field effect device, with a source terminal 100 connected directly to

signal from the source voltage 18 is directly connected to the source terminal 100 of

transistor 82. Likewise, the gate terminal 103 is connected to reference 107 which

may be the identical to reference 106 (supply voltage (V_{SS},), ground, or zero volt

reference) or just the reference of the ESD application. For purposes of clarity, Vss

With reference now to Figure 2A, therein is shown an ESD input protection

input path 12 which, in turn, is connected to pad 16. The device to be protected (not shown) has an input terminal 14 which is likewise coupled to path 12. The drain terminal 102 of the transistor 82 is shown coupled to drain voltage (V_{dd})while the gate 103 and substrate 104 terminals are connected to reference. In particular, substrate terminal 104 is connected to reference point 106 which may be the supply voltage (V_{SS}), ground, or zero volt reference of the ESD application. Thus, the input



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refers to the lowest potential supply voltage.